



STP14NF06

N-CHANNEL 60V - 0.1Ω - 14A TO-220

STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP14NF10	60 V	< 0.12 Ω	14 A

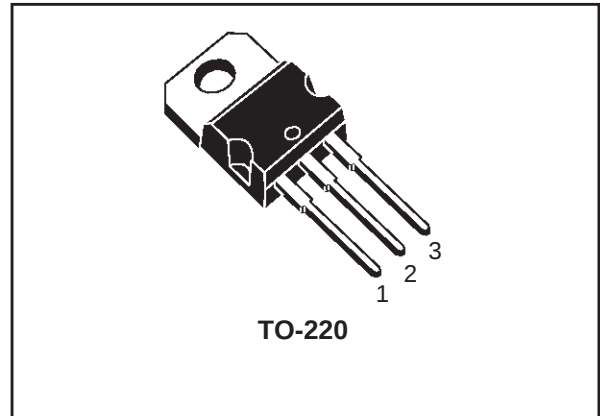
- TYPICAL R_{DS(on)} = 0.1Ω
- EXCEPTIONAL dv/dt CAPABILITY
- LOW GATE CHARGE AT 100 °C
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

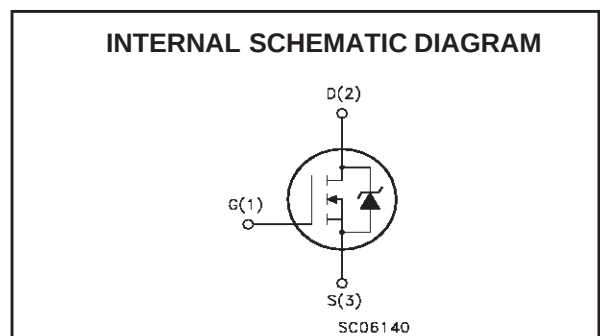
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- AUTOMOTIVE ENVIRONMENT



TO-220



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate- source Voltage	±20	V
I _D	Drain Current (continuous) at T _C = 25°C	14	A
I _D	Drain Current (continuous) at T _C = 100°C	10	A
I _{DM} (●)	Drain Current (pulsed)	56	A
P _{TOT}	Total Dissipation at T _C = 25°C	45	W
	Derating Factor	0.3	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	6	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	50	mJ
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 7A, di/dt ≤ 300A/μs, V_{DD} ≤ V(BR)DSS, T_j ≤ T_{JMAX}.

(2) Starting T_j = 25°C, I_D = 114A, V_{DD} = 15V

STP14NF06

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	3.33	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	2			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 7 A		0.10	0.12	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)} max, V _{GS} = 10V	14			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 7 A		7		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		361		pF
C _{oss}	Output Capacitance			54		pF
C _{rss}	Reverse Transfer Capacitance			21		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V, I_D = 7A$		12.5		ns
t_r	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		32		ns
Q_g	Total Gate Charge	$V_{DD} = 48V, I_D = 14A,$		11.2	15	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10V$		3.7		nC
Q_{gd}	Gate-Drain Charge			3.2		nC

SWITCHING OFF

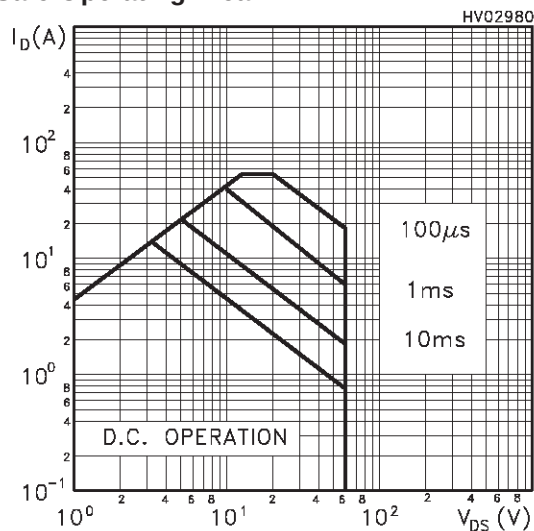
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 30V, I_D = 7A,$		30		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		9.5		ns

SOURCE DRAIN DIODE

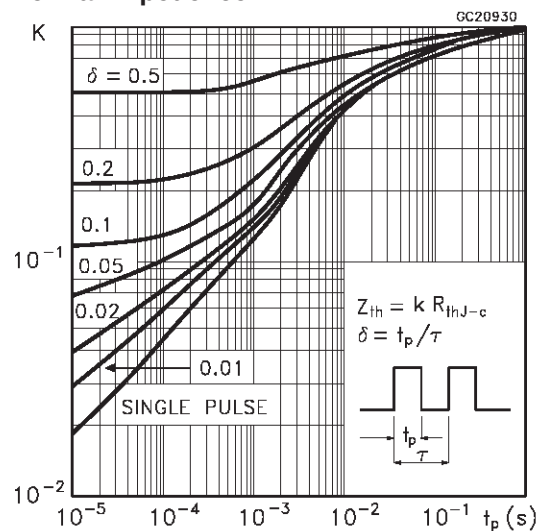
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				14	A
$I_{SDM(1)}$	Source-drain Current (pulsed)				56	A
$V_{SD(2)}$	Forward On Voltage	$I_{SD} = 14A, V_{GS} = 0$			1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 14A, di/dt = 100A/\mu s,$		38		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 30V, T_J = 150^\circ C$		61		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		3.2		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

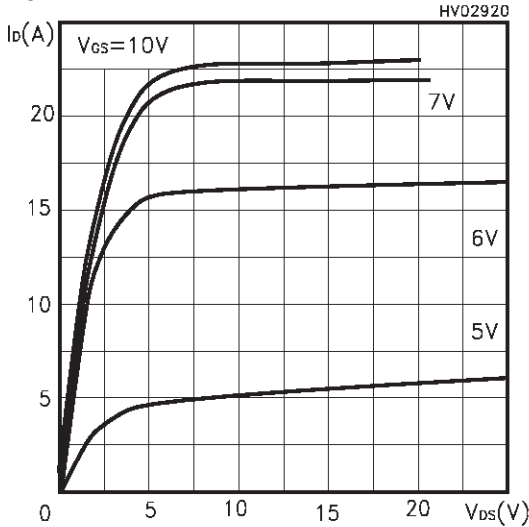
Safe Operating Area



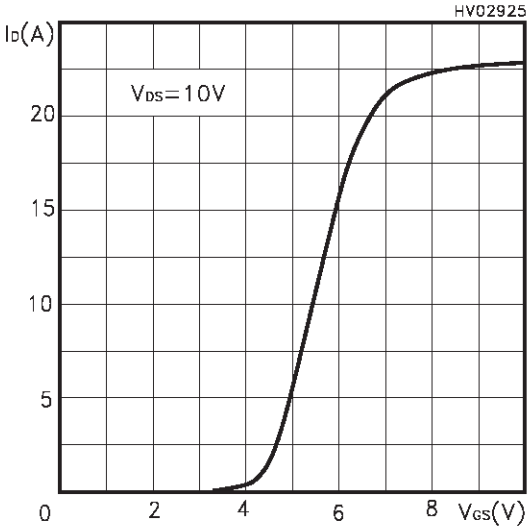
Thermal Impedance



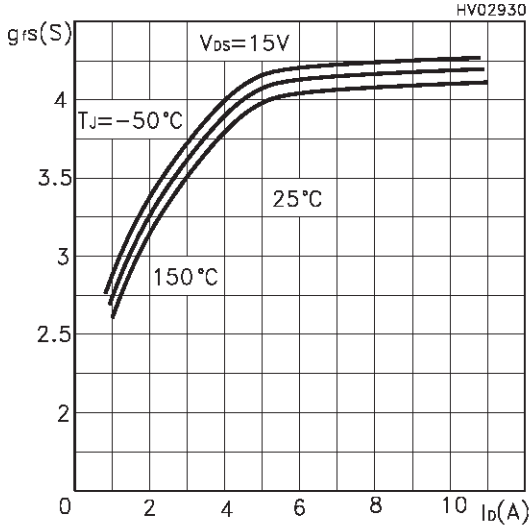
Output Characteristics



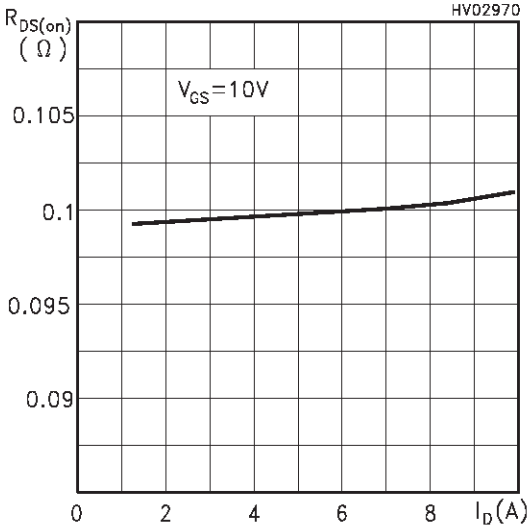
Transfer Characteristics



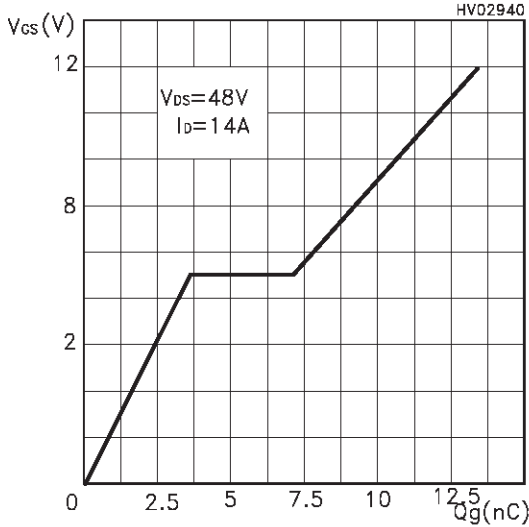
Transconductance



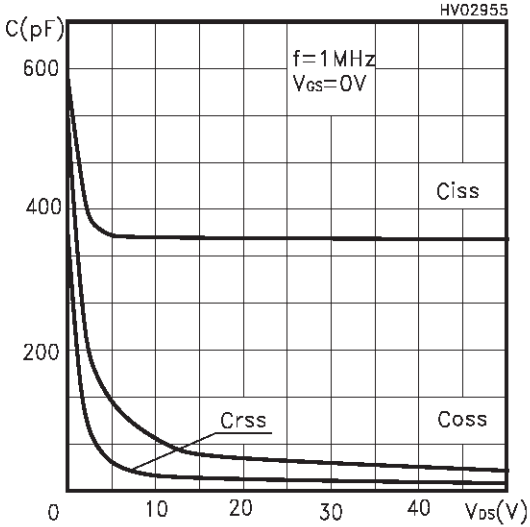
Static Drain-source On Resistance



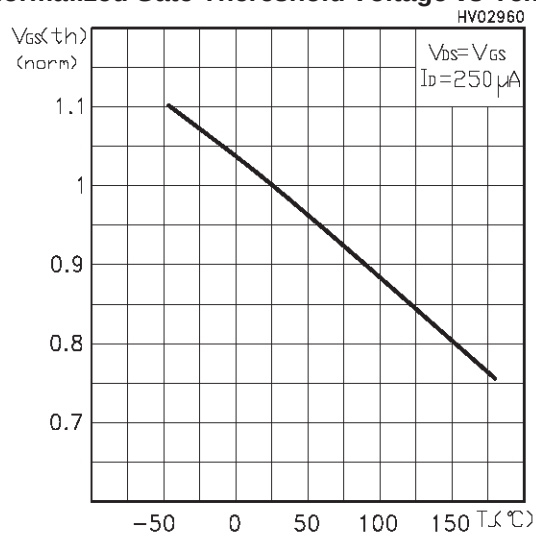
Gate Charge vs Gate-source Voltage



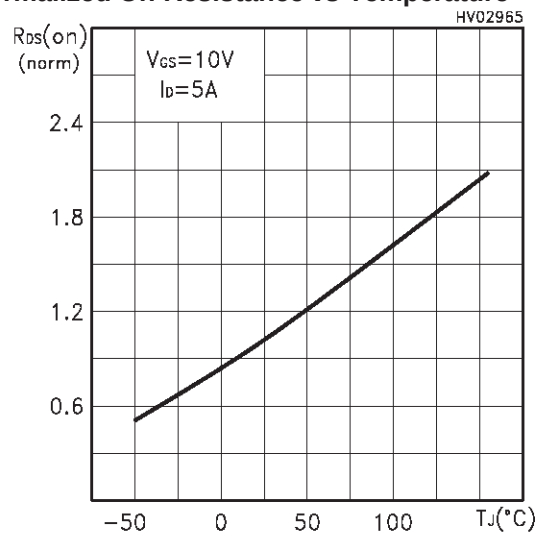
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

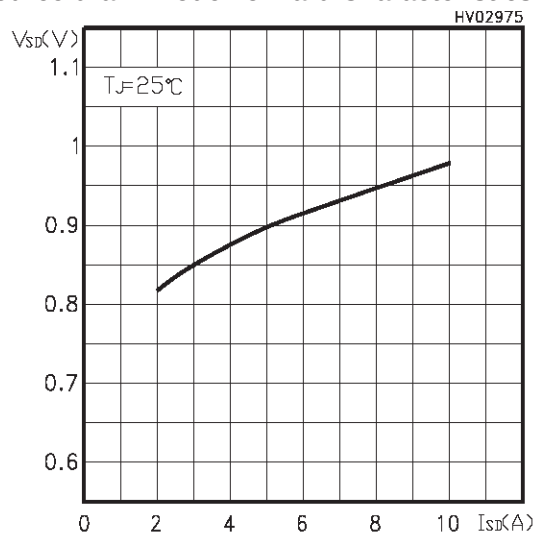
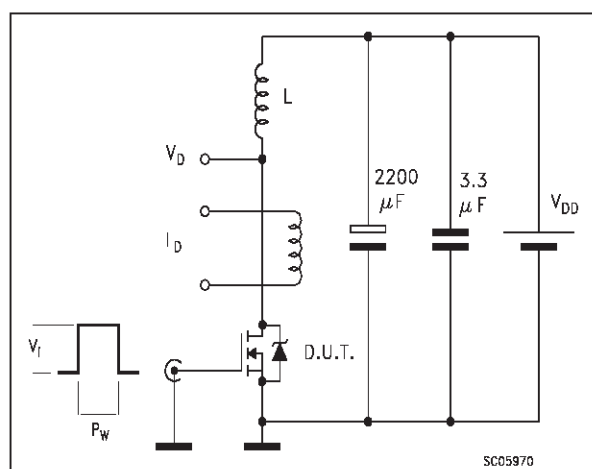
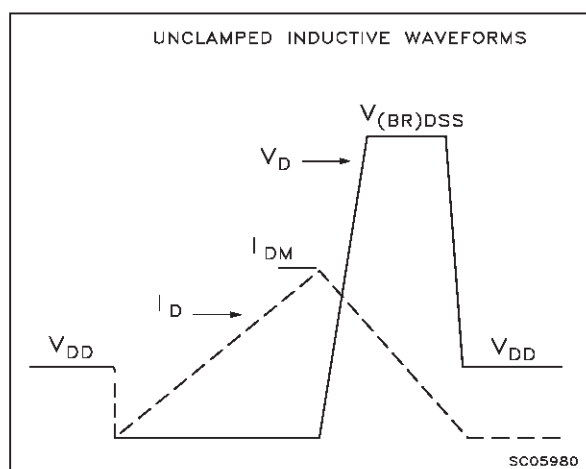
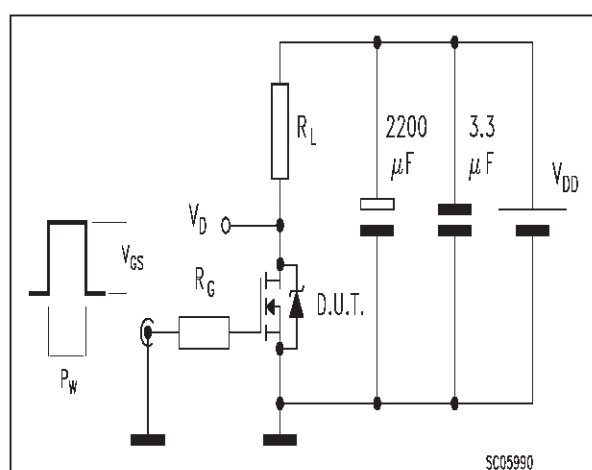
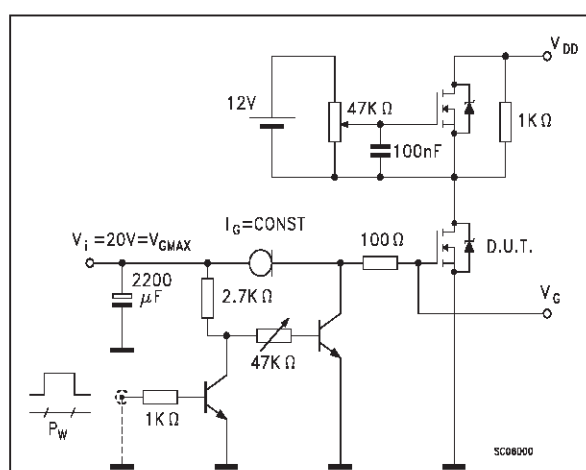
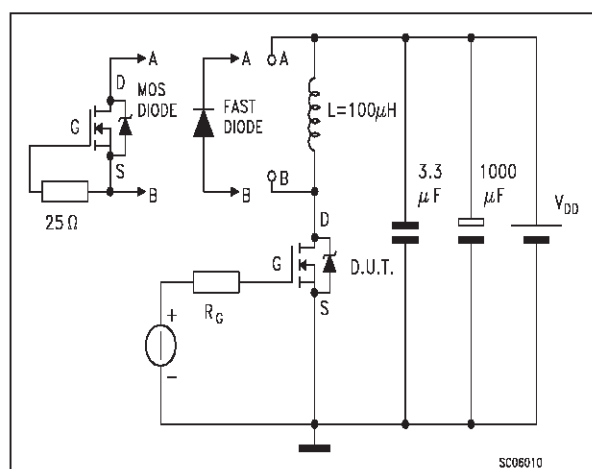
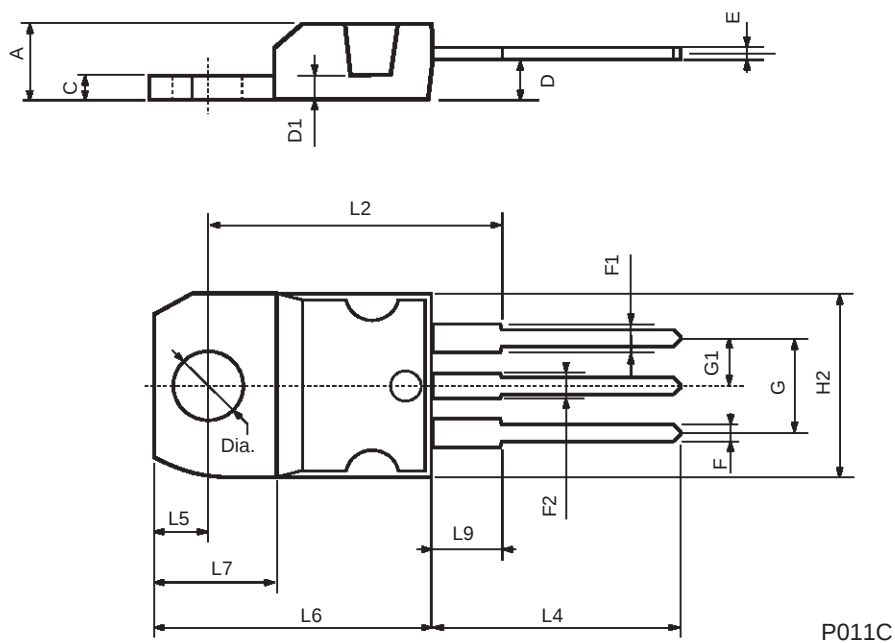


Fig. 1: Unclamped Inductive Load Test Circuit**Fig. 2: Unclamped Inductive Waveform****Fig. 3: Switching Times Test Circuit For Resistive Load****Fig. 4: Gate Charge test Circuit****Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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